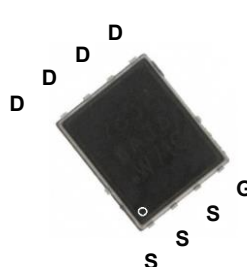
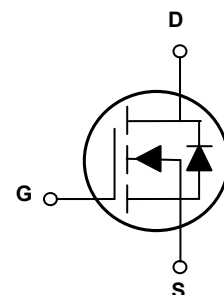


## Main Product Characteristics

$BV_{DSS}$	80V
$R_{DS(ON)}$	7.2m $\Omega$
$I_D$	80A



PPAK5x6



Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The GSFP8976 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	+20/-12	V
Drain Current-Continuous ( $T_C=25^\circ\text{C}$ )	$I_D$	80	A
Drain Current-Continuous ( $T_C=100^\circ\text{C}$ )		50	A
Drain Current-Pulsed <sup>1</sup>	$I_{DM}^1$	320	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	201	mJ
Single Pulse Avalanche Current <sup>2</sup>	$I_{AS}$	64	A
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	125	W
Power Dissipation-Derate Above 25 $^\circ\text{C}$		1	W/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$
Storage Temperature Range	$T_{STG}$	-55 To +150	$^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-55 To +150	$^\circ\text{C}$

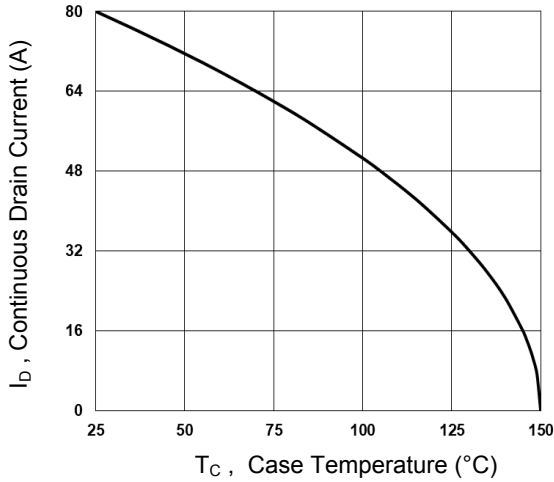
**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	80	-	-	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	-	-	1	$\mu A$
		$V_{DS}=64V, V_{GS}=0V, T_J=125^{\circ}\text{C}$	-	-	10	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=+20V, V_{DS}=0V$	-	-	100	nA
<b>On Characteristics</b>						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	5.8	7.2	m $\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.2	4	V
Forward Transconductance	$g_{fs}$	$V_{DS}=10V, I_D=3A$	-	10	-	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>3,4</sup>	$Q_g$	$V_{DS}=40V, I_D=10A, V_{GS}=10V$	-	40.3	60	nC
Gate-Source Charge <sup>3,4</sup>	$Q_{gs}$		-	9.4	15	
Gate-Drain Charge <sup>3,4</sup>	$Q_{gd}$		-	16	25	
Turn-On Delay Time <sup>3,4</sup>	$t_{d(on)}$	$V_{DD}=40V, R_G=6\Omega, V_{GS}=10V, I_D=1A$	-	14.6	30	nS
Rise Time <sup>3,4</sup>	$t_r$		-	21.5	42	
Turn-Off Delay Time <sup>3,4</sup>	$t_{d(off)}$		-	52	108	
Fall Time <sup>3,4</sup>	$t_f$		-	83.5	167	
Input Capacitance	$C_{iss}$	$V_{DS}=40V, V_{GS}=0V, F=1\text{MHz}$	-	2490	4980	pF
Output Capacitance	$C_{oss}$		-	823	1640	
Reverse Transfer Capacitance	$C_{rss}$		-	44	80	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	1	-	$\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_S$	$V_G=V_D=0V, \text{Force Current}$	-	-	80	A
Pulsed Source Current	$I_{SM}$		-	-	160	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	-	-	1	V
Reverse Recovery Time	$T_{rr}$	$V_{GS}=10V, I_S=10A, di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	-	50	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	70	-	nC

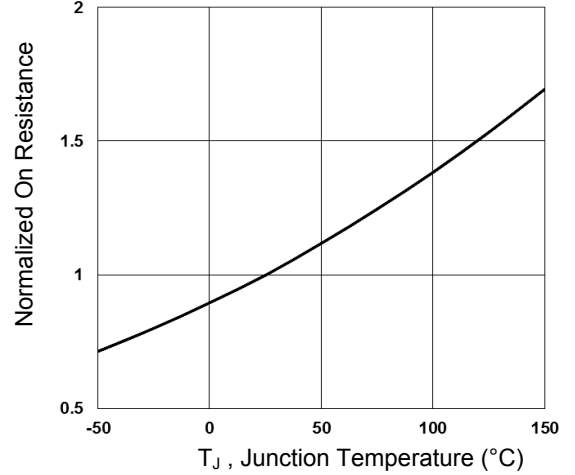
Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=40V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=64A, R_G=25\Omega, \text{starting } T_J=25^{\circ}\text{C}$ .
3. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
4. Essentially independent of operating temperature.

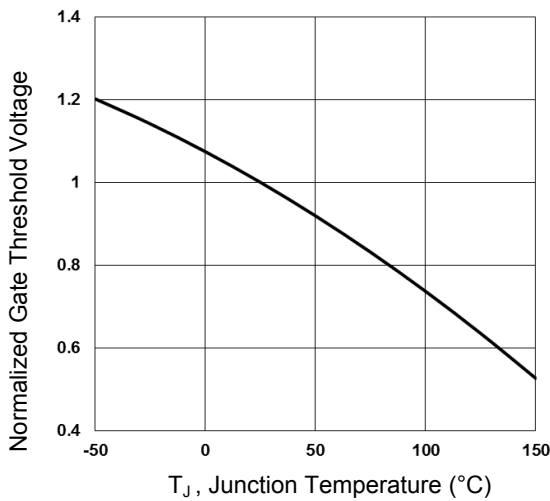
### Typical Electrical and Thermal Characteristic Curves



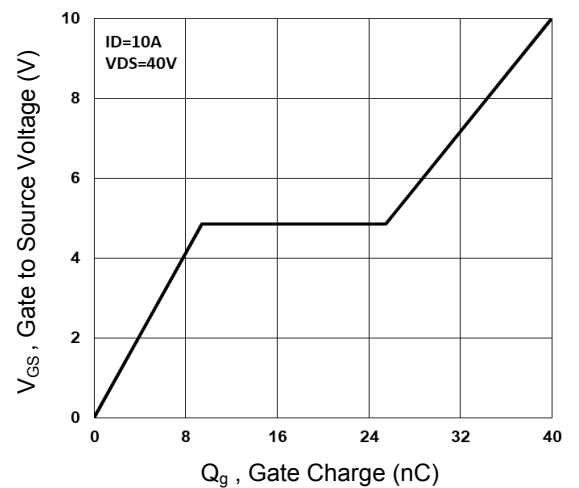
**Figure 1. Continuous Drain Current vs. T<sub>c</sub>**



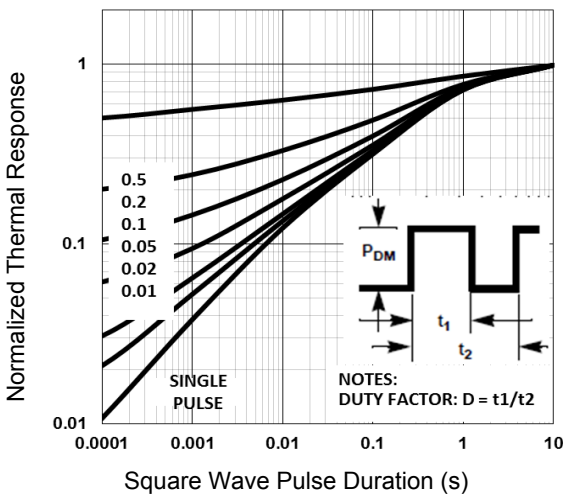
**Figure 2. Normalized R<sub>DS(on)</sub> vs. T<sub>j</sub>**



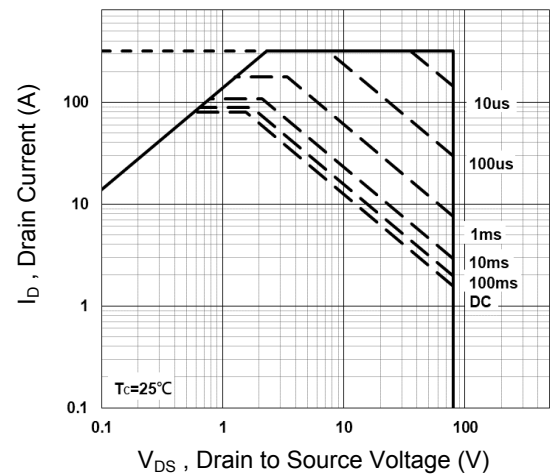
**Figure 3. Normalized V<sub>th</sub> vs. T<sub>j</sub>**



**Figure 4. Gate Charge Characteristics**

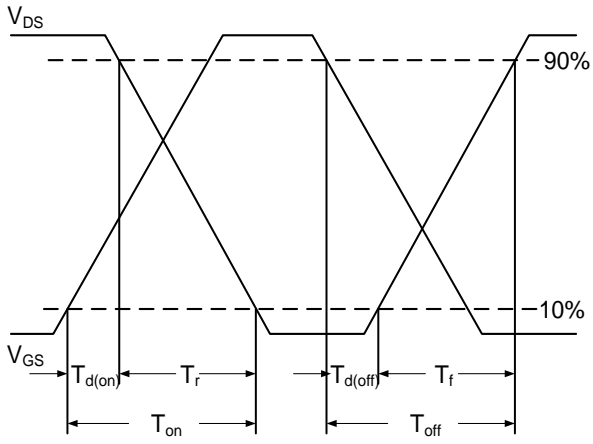


**Figure 5. Normalized Transient Impedance**

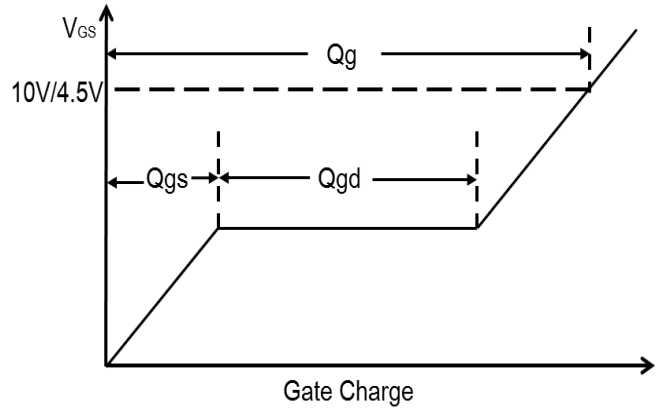


**Figure 6. Maximum Safe Operation Area**

**Typical Electrical and Thermal Characteristic Curves**



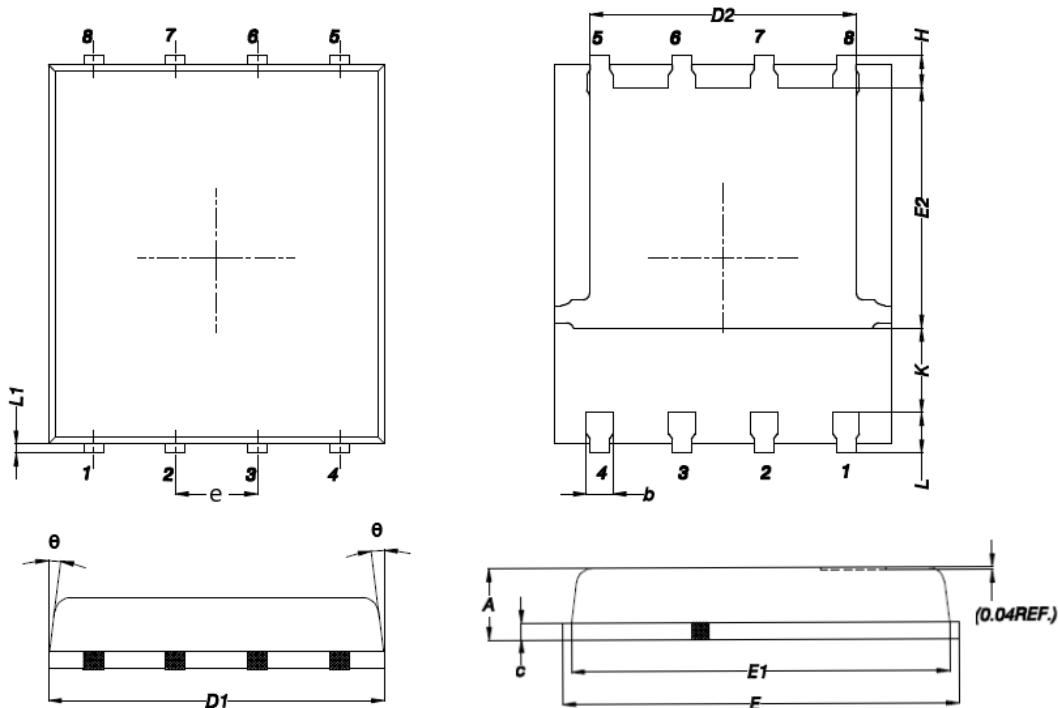
**Fig.7 Switching Time Waveform**



**Fig.8 Gate Charge Waveform**

**Package Outline Dimensions**

**PPAK5x6**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.200	0.850	0.047	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.400	4.800	0.212	0.189
D2	4.310	3.610	0.170	0.142
E	6.300	5.850	0.248	0.230
E1	5.960	5.450	0.235	0.215
E2	3.920	3.300	0.154	0.130
e	1.27BSC		0.05BSC	
H	0.650	0.380	0.026	0.015
K	---	1.100	---	0.043
L	0.710	0.380	0.028	0.015
L1	0.250	0.050	0.009	0.002
θ	12°	0°	12°	0°